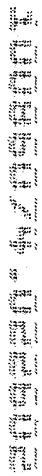


[illegible][illegible]

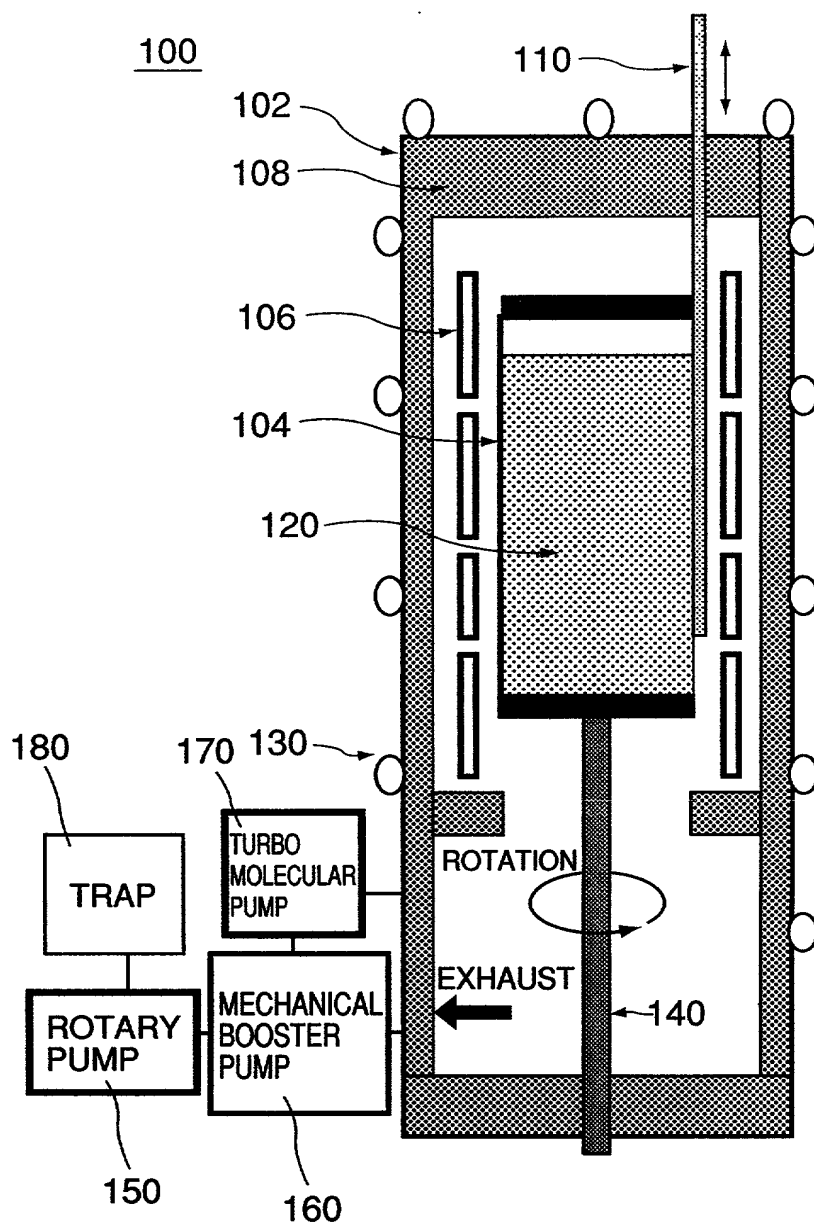


FIG. 2

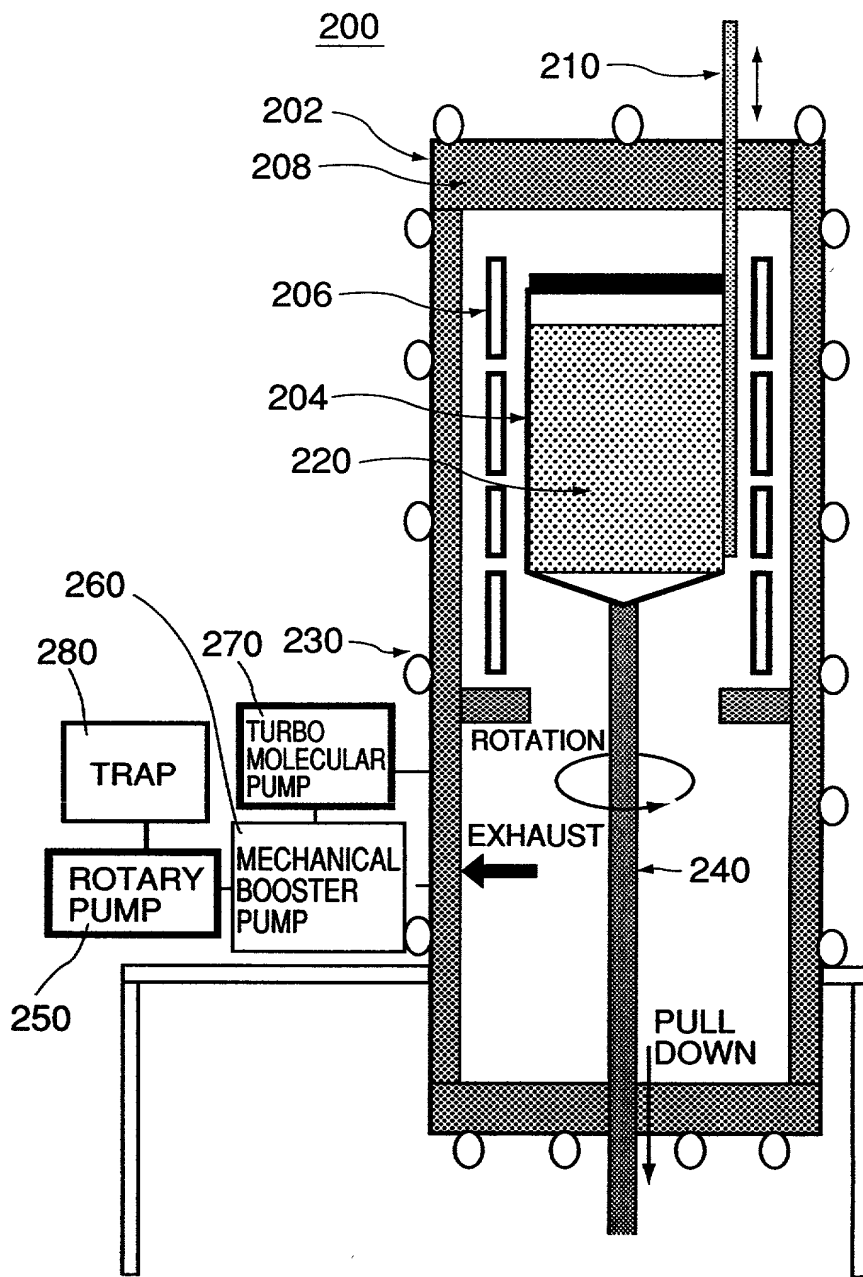


FIG. 3

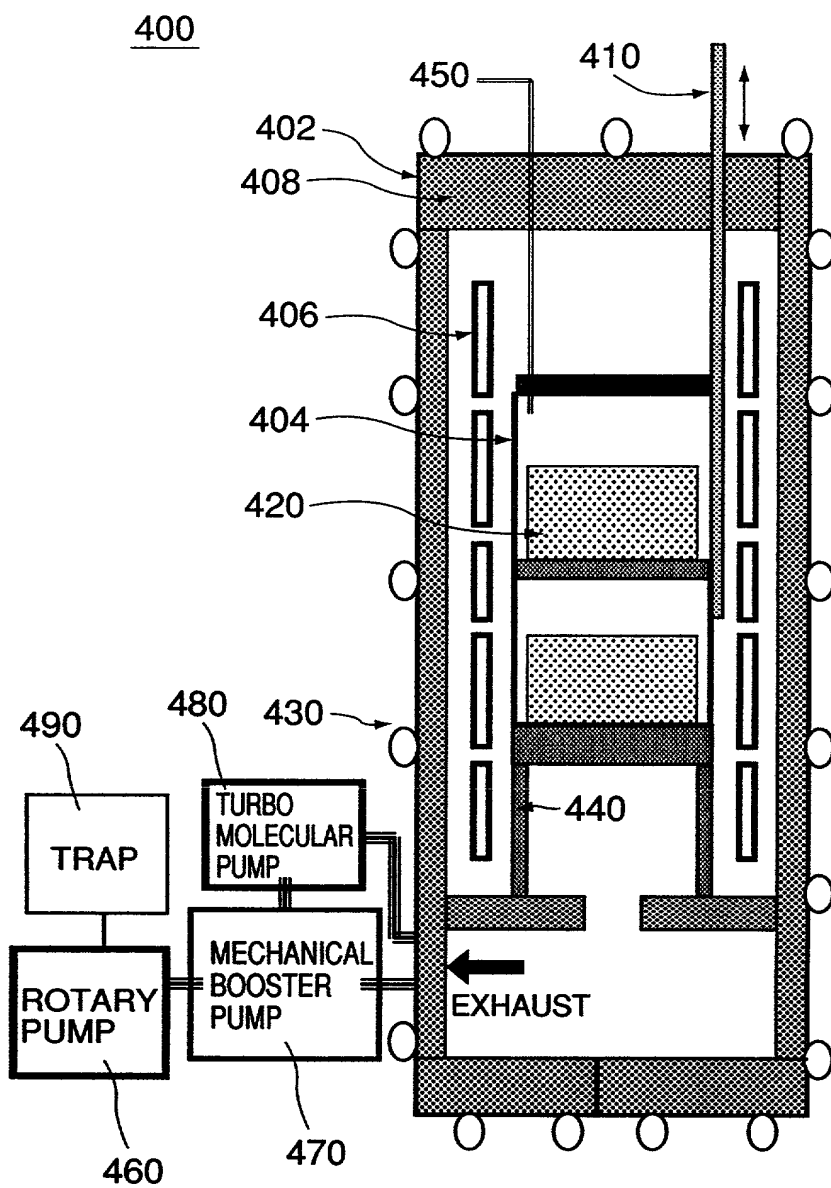


FIG. 4

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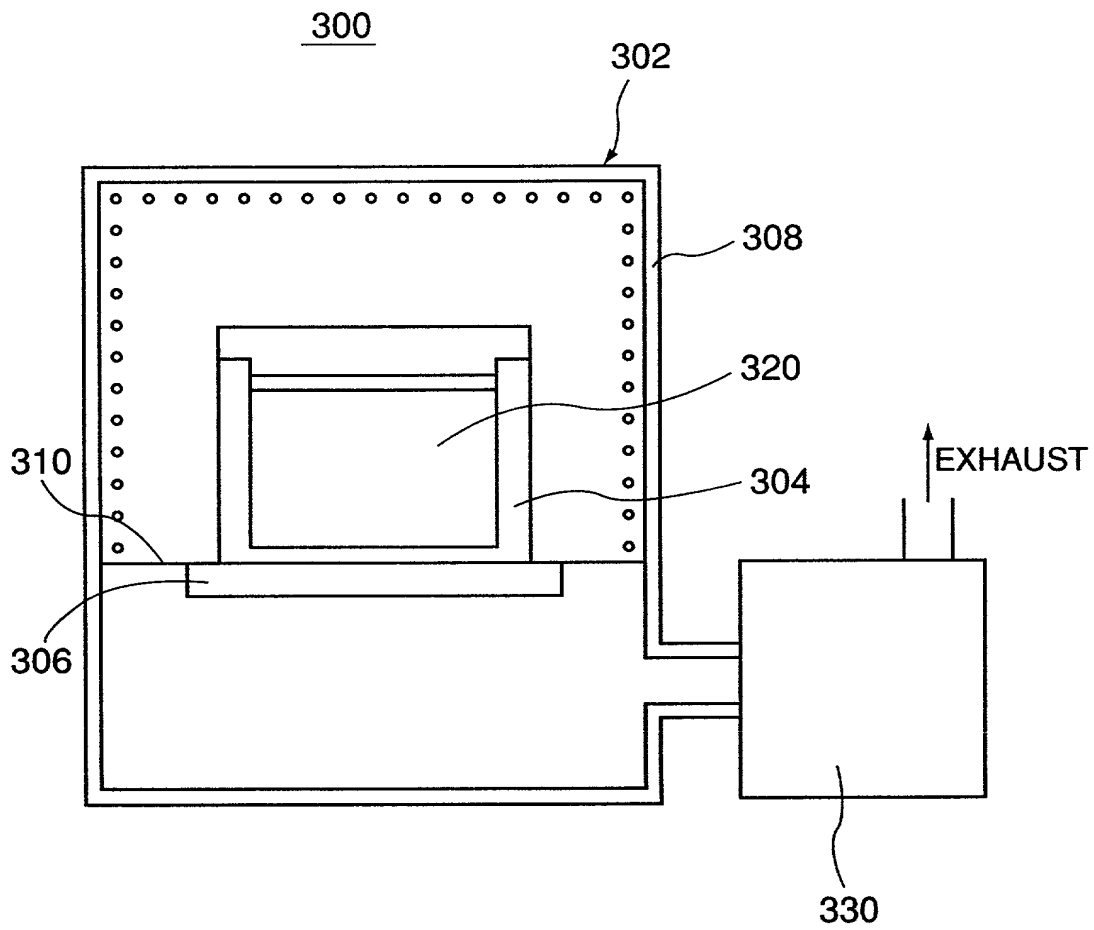
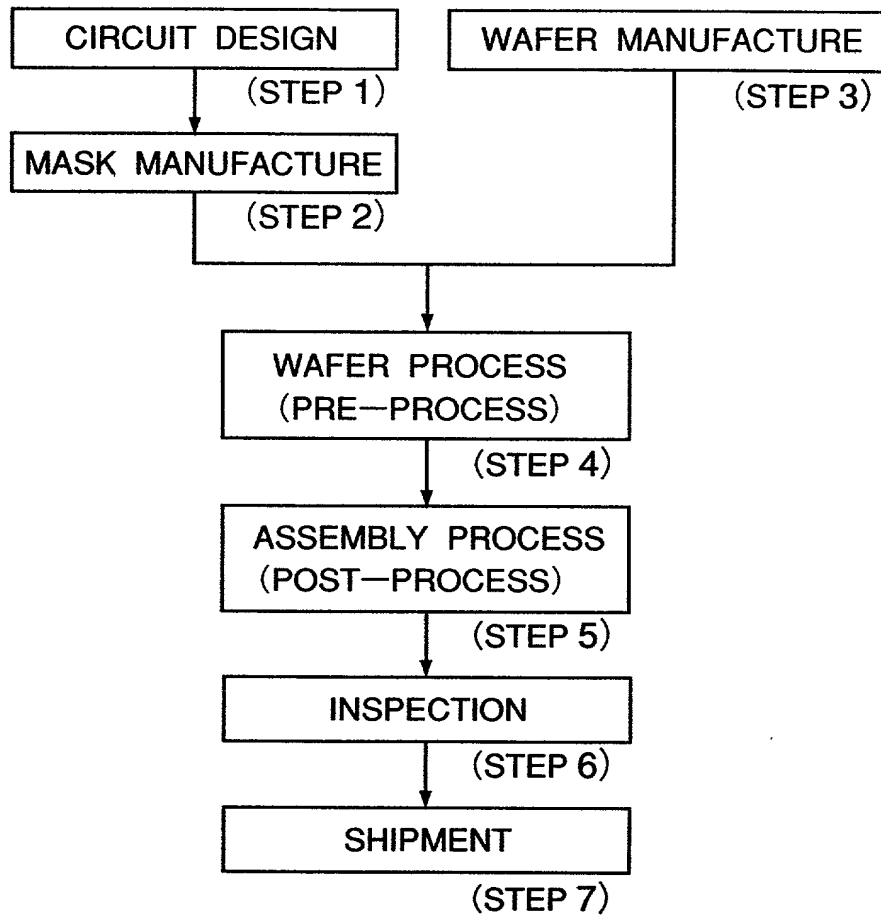


FIG. 5





**FIG. 7**

```
graph TD; S11[OXIDATION  
(STEP 11)] --> S12[CVD  
(STEP 12)]; S12 --> S13[ELECTRODE  
FORMATION  
(STEP 13)]; S13 --> S14[ION IMPLANTATION  
(STEP 14)]; S14 --> S15[RESIST PROCESS  
(STEP 15)]; S15 --> S16[EXPOSURE  
(STEP 16)]; S16 --> S17[DEVELOPMENT  
(STEP 17)]; S17 --> S18[ETCHING  
(STEP 18)]; S18 --> S19[RESIST  
SEPARATION  
(STEP 19)]; S19 --> REPEAT[REPEAT]; REPEAT --> S11;
```

The flowchart illustrates a manufacturing process for a semiconductor device, consisting of the following steps:

- OXIDATION (STEP 11)
- CVD (STEP 12)
- ELECTRODE FORMATION (STEP 13)
- ION IMPLANTATION (STEP 14)
- RESIST PROCESS (STEP 15)
- EXPOSURE (STEP 16)
- DEVELOPMENT (STEP 17)
- ETCHING (STEP 18)
- RESIST SEPARATION (STEP 19)

The process is a loop: after RESIST SEPARATION (STEP 19), the flow returns to OXIDATION (STEP 11), labeled "REPEAT".

**FIG. 8**